

Semiclassical theory of shot noise in disordered SN contacts

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We present a semiclassical theory of shot noise in diffusive superconductor - normal metal contacts. At subgap voltages, we reproduce the doubling of shot noise with respect to conventional normal-metal contacts, which is interpreted in terms of an energy balance of electrons. Above the gap, the voltage dependence of the noise crosses over to the standard one with a voltage-independent excess noise. The semiclassical description of noise leads to correlations between currents at different electrodes of multiterminal SN contacts which are always of fermionic type, i.e. negative. Using a quantum extension of the Boltzmann - Langevin method, we reproduce the peculiarity of noise at the Josephson frequency and obtain an analytical frequency dependence of noise at above-gap voltages.

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In recent years, the noise properties of hybrid contacts involving superconducting (S) and normal (N) metals attracted considerable attention.¹ Theoretical work in this direction was pioneered by Khlus,² who found that Andreev reflection,³ in which electrons incoming from normal metals are reflected from the SN interface as holes, play a key role in the shot noise of SN structures. For clean SN contacts, he predicted that the shot noise vanishes at subgap voltages $eV < \Delta$. de Jong and Beenakker⁴ addressed dirty SN contacts and found that the shot noise at subgap voltages is doubled with respect to its value in a normal contact with the same resistance. This doubling of shot noise has already been experimentally confirmed.^{5,6} The distribution function of current fluctuations was calculated and it was found that at subgap voltages, it describes independent transfers of discrete charge $2e$ through the contact.⁷ Lesovik *et al.*⁸ found that the frequency dependence of the shot noise exhibits a peculiarity at the Josephson frequency $\omega = 2eV$ instead of $\omega = eV$ in normal contacts. More recently, the same authors obtained additional singularities in the frequency dependence of the noise at above-gap voltages.⁹ These results could lead to the impression that the motion of electrons and holes is correlated not only at the SN interface, but that the current is carried also through the normal part of the contact in portions of $2e$ instead of e . Recent findings that the correlations of currents at two normal contacts attached to a superconductor may be positive,^{10,11} as in the case of Bose statistics seemed to reinforce such a view. On the other hand, from these works it is not clear whether the above results require phase coherence of electrons nor if there are restrictions for the contact length.

Recently, Gramespacher and one of the authors¹² discussed the fluctuations in multiterminal SN contacts using electronlike and holelike distribution functions, which were expressed in terms of quantum-mechanical

injectivities¹³ of the terminals. It was shown there, in particular, that positive correlations vanish in the limit of a large channel number. In this paper, we present a semiclassical theory of shot noise in disordered SN contacts. We show that the doubling of shot noise may be obtained within a simple Boltzmann - Langevin approach¹⁴ provided that the appropriate boundary conditions for the average distribution function are used. We relate the increase in the shot noise to the peculiar energy transport through an SN interface and show that this effect is stable with respect to phase-breaking. From the semiclassical nature of electron transport in the N region, it immediately follows that the correlations between currents in different electrodes of a multiterminal diffusive SN contact are always negative. We are also able to explain the peculiarities of the frequency dependence of noise in terms of the shape of the electron distribution function.

Consider a narrow normal-metal microbridge connecting massive normal and superconducting electrodes. The

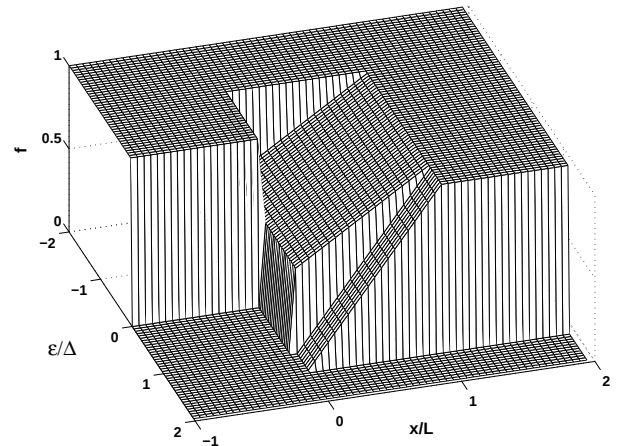


FIG. 1. The non-equilibrium electron distribution function in the normal part of an NS contact at voltage $eV = 1.4\Delta$.

elastic mean free path l of electrons in the microbridge is assumed to be short and the length of the contact L is assumed to be much larger than $(\hbar D/\Delta)^{1/2}$, where Δ is the superconducting gap and D is the diffusion coefficient in the normal metal. The applied voltage or temperature are considered to be much larger than the Thouless energy $\varepsilon_T = \hbar D/L^2$. Under these conditions, it is possible to neglect the penetration of the condensate into the microbridge and consider it just as a normal metal with a nonequilibrium distribution function of electrons.^{15,16}

Let the x axis be directed along the contact, $x = 0$ corresponding to the superconducting electrode, and $x = L$, to the normal-metal one. The electron energy ε in the normal metal is measured from the Fermi level of the superconductor. Introduce an energy-dependent coefficient W of normal transmission of an electron from the contact through the NS interface without being Andreev reflected, so that $W(\varepsilon) = 0$ if $|\varepsilon| < \Delta$ and $W(\varepsilon) \rightarrow 1$, for $|\varepsilon| \gg \Delta$.

Since the electrons in the superconducting electrode are described by an equilibrium Fermi distribution function $f_0(\varepsilon)$, the distribution function of electrons moving into the contact from the SN interface may be written in the form^{17,18}

$$f(\varepsilon, v_x) = W f_0(\varepsilon) + (1 - W)[1 - f(-\varepsilon, -v_x)], \quad (1)$$

for $\varepsilon > 0$ and $v_x > 0$, and the distribution function of holes moving into the contact from the interface may be written in the form

$$1 - f(\varepsilon, v_x) = W[1 - f_0(\varepsilon)] + (1 - W)f(-\varepsilon, -v_x), \quad (2)$$

for $\varepsilon < 0$ and $v_x > 0$. Since in the bulk of the contact the electron motion is diffusive, we must now obtain a suitable boundary condition at the NS interface for the diffusion equation.

Introduce the symmetric and antisymmetric parts of f with respect to v_x :

$$\begin{aligned} f_s(\varepsilon) &= (1/2) [f(\varepsilon, v_x) + f(\varepsilon, -v_x)], \\ f_a(\varepsilon) &= (1/2) [f(\varepsilon, v_x) - f(\varepsilon, -v_x)]. \end{aligned} \quad (3)$$

$$f(\varepsilon, x) = \begin{cases} \frac{1}{2} \left(1 + \frac{x}{L}\right) f_0(\varepsilon - eV) + \frac{1}{2} \left(1 - \frac{x}{L}\right) f_0(\varepsilon + eV), & |\varepsilon| < \Delta \\ \left(1 - \frac{x}{L}\right) f_0(\varepsilon) + \frac{x}{L} f_0(\varepsilon - eV), & |\varepsilon| > \Delta. \end{cases} \quad (10)$$

At subgap voltages, the shape of the distribution function is exactly the same as if the contact were extended in negative direction from 0 to $-L$ and the voltage $-V$ were applied at this point.⁴ The distribution function for

Inside the contact, the distribution function obeys the diffusion equation and may be represented as a sum of an isotropic part $f(\varepsilon, x)$ and a small anisotropic part

$$f_1 = -(v_x/v_F)(l/L)[f(\varepsilon, L) - f(\varepsilon, 0)]. \quad (4)$$

Following Kupriyanov and Lukichev,¹⁹ we equate now $f(\varepsilon, 0)$ to $f_s(\varepsilon)$ and f_1 to $(v_x/v_F)f_a(\varepsilon)$. Introducing the distribution function of electrons in the normal electrode $f_n(\varepsilon)$, one may express f_a in terms of f_s and f_n :

$$f_a(\varepsilon) = (l/L)[f_s(\varepsilon) - f_n(\varepsilon)]. \quad (5)$$

For the sake of definiteness, assume now $\varepsilon > 0$. By substituting Eqs. (3) into Eqs. (1) for $f(\varepsilon, v_x)$ and (2) for $1 - f(-\varepsilon, v_x)$ and excluding f_a from them by means of (5), one obtains a closed set of equations for $f_s(\varepsilon)$ and $f_s(-\varepsilon)$:

$$\begin{aligned} (1 + l/L) f_s(\varepsilon) + (1 - W)(1 - l/L) f_s(-\varepsilon) &= 1 - W f_0(-\varepsilon) \\ + (l/L) f_n(\varepsilon) - (l/L)(1 - W) f_n(-\varepsilon) \end{aligned} \quad (6)$$

and the equation obtained from it by interchanging ε and $-\varepsilon$. The solution of the set (6) assumes different forms depending on the relationship between W and l/L . In the subgap region $|\varepsilon| < \Delta$, $W = 0$ and we obtain

$$f_s(\varepsilon) = \frac{1}{2} [1 + f_n(\varepsilon) - f_n(-\varepsilon)] \quad (7)$$

for both signs of ε . Suppose that the normal electrode has a potential V . Then $f_n(\varepsilon) = f_0(\varepsilon - eV)$, and inside the gap,

$$f_s(\varepsilon) = \frac{1}{2} [f_0(\varepsilon - eV) + f_0(\varepsilon + eV)], \quad |\varepsilon| < \Delta. \quad (8)$$

Outside the subgap region, $W \neq 0$, and l/L may be neglected with respect to it virtually at all energies. In this case, one easily obtains

$$f_s(\varepsilon) = f_0(\varepsilon), \quad |\varepsilon| > \Delta. \quad (9)$$

Inside the contact, the distribution function is obtained by solving the diffusion equation with the boundary conditions (8) and (9). As a result, one obtains:

an above-gap voltage is shown in Fig. 1. Note that at finite voltages, $f(\varepsilon)$ is discontinuous at $|\varepsilon| = \Delta$ even at nonzero temperature.

Consider now the noise of the contact. Since all the

voltage drop takes place inside the normal-metal microbridge and there is no voltage drop across the SN interface, it is reasonable to assume that all the noise is produced by random impurity scattering in the microbridge only. In this case, we can use the well known Langevin equations for the current fluctuations,²⁰

$$\delta \mathbf{j} = -D \frac{\partial}{\partial \mathbf{r}} \delta \rho - \sigma \frac{\partial}{\partial \mathbf{r}} \delta \phi + \delta \mathbf{j}^{ext}, \quad (11)$$

where D is the diffusion coefficient, σ is the electric conductivity, $\delta \rho(\mathbf{r})$ is the charge-density fluctuation, $\delta \phi(\mathbf{r})$ is the local fluctuation of the electric potential, and the correlator of extraneous currents $\delta \mathbf{j}^{ext}$ is given by

$$\langle \delta j_{\alpha}^{ext}(\mathbf{r}_1) \delta j_{\beta}^{ext}(\mathbf{r}_2) \rangle_{\omega} = 4\sigma \delta_{\alpha\beta} \delta(\mathbf{r}_1 - \mathbf{r}_2) T_N(\mathbf{r}_1),$$

$$S_I = 4 \frac{T}{R} \left\{ \frac{2}{3} + \frac{1}{3} \frac{eV}{T} \coth \left(\frac{eV}{T} \right) + \frac{1}{6} \left[\tanh \left(\frac{\Delta + eV}{2T} \right) + \tanh \left(\frac{\Delta - eV}{2T} \right) - 2 \tanh \left(\frac{\Delta}{2T} \right) \right] + \frac{1}{6} \left[\coth \left(\frac{eV}{2T} \right) - 2 \coth \left(\frac{eV}{T} \right) \right] \ln \left[\frac{\exp(\Delta/T) + \exp(eV/T)}{\exp(\Delta/T) + \exp(-eV/T)} \right] \right\}. \quad (14)$$

At zero voltage, this expression reduces to the Nyquist formula $S_I = 4T/R$. At zero temperature yet finite voltage, Eqn. (14) takes a very simple form:

$$S_I = \frac{4}{3} \frac{e|V|}{R} + \frac{2}{3} \theta(e|V| - \Delta) \frac{\Delta - e|V|}{R}. \quad (15)$$

The shot noise in diffusive SN contacts is doubled at voltages $e|V| < \Delta$ as compared to the same contacts between normal metals. The reasons for the shot-noise doubling can be understood in terms of the noise temperature of electrons T_N and the energy transport. The electrons in the contact acquire additional energy because of their acceleration by the field. If both electrodes are made of normal metal, the excess energy flows into both electrodes thus effectively cooling the contact and decreasing T_N . However if one of the electrodes is superconducting, the SN boundary forbids heat transfer in the subgap region.²² The absence of heat transfer through an SN boundary has been known for many years, and this is precisely what motivated the pioneering paper by Andreev.³ Because there is only one energy drain now instead of two, naturally T_N is higher than in the case of a normal contact.

The above semiclassical derivation shows that the doubling of shot noise is insensitive to phase-breaking. In the case of strong electron-electron scattering, the effective-temperature approximation may be used at $eV \ll \Delta$ and precisely the same heat-balance equation for the effective temperature T_e as in normal contacts^{23,24} can be written except that the heat-absorption boundary condition $T_e = T$ at the SN interface should be replaced by the zero heat-flux condition $\partial T_e / \partial x = 0$. It is easily seen that this should double the shot noise making it

$$T_N(\mathbf{r}) = \int d\varepsilon f(\varepsilon, \mathbf{r}) [1 - f(\varepsilon, \mathbf{r})]. \quad (12)$$

At sufficiently low frequencies, the fluctuation of the total current $\delta \mathbf{j}$ may be considered as constant along the contact, and Eqn. (11) may be integrated over its length. As a result, the gradient terms in (11) drop out because of the boundary conditions $\delta \rho = 0$ and $\delta \phi = 0$, and one arrives at the standard expression for the noise in disordered metal contacts:²¹

$$S_I = \frac{4}{R} \int \frac{dx}{L} T_N(x), \quad (13)$$

where R is the normal resistance of the contact. Substituting now the distribution function (10) into (13) and performing the integration, one obtains that

$2 \times (\sqrt{3}/2)eI = \sqrt{3}eI$ and thus increasing it above the noninteracting-electron value precisely as for a normal contact.^{23,24} Much like in the case of normal contacts, the noise should be suppressed by energy relaxation caused e. g. by phonon emission.

Using the semiclassical approach, Sukhorukov and Loss²⁵ recently investigated the correlations between currents in different contacts of multiterminal diffusive normal-metal systems. Here we extend their discussion to the case of multiterminal SN systems.²⁶ It is convenient to introduce characteristic potentials¹³ $\phi_n(\mathbf{r})$, $n = 1, \dots, N$ associated with each contact n which equal 1 at contact n and are zero at all other electrodes obeying the equation

$$\nabla(\sigma \nabla \phi_n) = 0 \quad (16)$$

in the bulk of the contact. In terms of these potentials, the normal-state conductance matrix of the contact may be written in the form

$$G_{mn} = - \int d\mathbf{S}_m \cdot \sigma \phi_m \nabla \phi_n, \quad (17)$$

where S_m is the interface of the system with electrode m , and the cross-correlated spectral density for contacts n and m may be written in the form²⁵

$$S_{mn} = 4 \int d^3\mathbf{r} \nabla \phi_n \cdot \nabla \phi_m \cdot \sigma T_N(\mathbf{r}). \quad (18)$$

Performing twice an integration by parts and making use of (16) and a similar equation for f in T_N , equation (18) is easily brought to a form

$$S_{mn} = -2G_{mn} T_N|_{S_m} - 2G_{nm} T_N|_{S_n}$$

$$-4 \int d^3r \phi_n \phi_m \sigma \int d\varepsilon (\nabla f)^2. \quad (19)$$

As T_N , G_{mn} , and ϕ_m are always positive, this proves that the current correlations are always negative, i. e. of fermionic type. As this proof holds for an arbitrary shape of the distribution function at the interfaces with electrodes, the correlations are negative for an arbitrary number of superconducting electrodes provided that the Josephson effect between them is suppressed.

Consider now the noise at frequencies $\omega \sim eV$. This is the range of quantum noise, which clearly cannot be described in terms of the Boltzmann equation. However it was recently shown that for disordered metals, the Langevin scheme may be extended to high frequencies by introducing a frequency-dependent noise temperature²⁷

$$T_N(\mathbf{r}, \omega) = \frac{1}{2} \int d\varepsilon \{ f(\mathbf{r}, \varepsilon) [1 - f(\mathbf{r}, \varepsilon + \omega)] + f(\mathbf{r}, \varepsilon + \omega) [1 - f(\mathbf{r}, \varepsilon)] \} \quad (20)$$

into Eq. (12). If the frequency is smaller than $1/RC$, where C is the capacity of the contact to all possible external gates, the current fluctuation may still be considered as constant along the contact length, and we arrive again at Eq. (13) with $T_N(x, \omega)$ substituted for $T_N(x)$. Note that the latter condition is well compatible with $\omega \gg D/L^2$ because $1/RC$ is larger by an extra factor containing the ratio of the contact diameter to the Thomas - Fermi screening length.

Suppose first that $eV < \Delta$. Integration in (20) and (13) then gives

$$S_I(\omega) = \frac{1}{3R} [4U(\omega) + U(2eV + \omega) + U(2eV - \omega)], \quad (21)$$

with $U(\omega) = \omega \coth(\omega/2T)$, which reduces to

$$S_I(\omega) = (1/3R) [4\omega + \max(4eV, 2\omega)] \quad (22)$$

at zero temperature. The frequency dependence of S_I exhibits a kink at $\omega = 2eV$, which would correspond to the Josephson frequency of the contact if the second electrode were also superconducting. The reason for the doubling of the kink frequency with respect to normal contacts is that the range of energies where the drop of the distribution function takes place is two times larger now.

In the case where $T = 0$ and $|eV| > \Delta$, integration gives

$$S_I(\omega) = \frac{|\omega|}{R} + \frac{1}{6R} (|\omega + 2\Delta| + |\omega - 2\Delta| + |\omega - eV + \Delta| + |\omega - eV - \Delta| + |\omega + eV + \Delta| + |\omega + eV - \Delta|). \quad (23)$$

in accordance with recent numerical results,⁹ this expression exhibits peculiarities at $\omega = 2\Delta$ and $\omega = eV \pm \Delta$, which are related with discontinuities in the energy dependence of the distribution function. The slope of $S(\omega)$ increases from $1/R$ at $\omega \rightarrow 0$ to $2/R$ at $\omega \rightarrow \infty$.

In this work we have developed a semi-classical approach for the noise in metallic diffusive NS-structures. This approach explains a number of key results in a physically transparent manner and demonstrates that these results are immune to dephasing.

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